

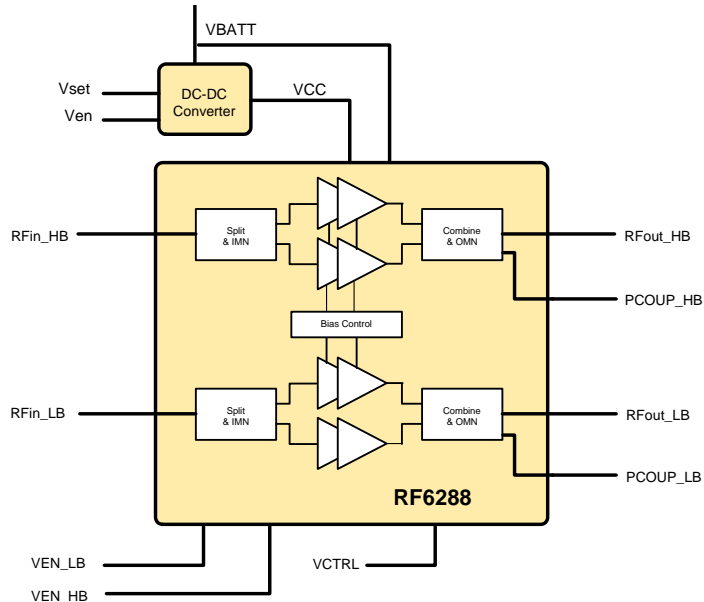


Features

- Dual-Path PA
UMTS Bands 1, 2, 4, 5, 8
- PA Load Insensitive
- Used with DC-DC Converter for Optimized Efficiency
- Analog Bias Control for Additional Current Savings
- Internal Voltage Regulator Eliminates the Need for External Reference Voltage (V_{REF})
- Integrated Blocking and Collector Decoupling Caps
- Integrated Coupler Outputs With Directivity

Applications

- UMTS Wireless Handsets
- UMTS Data Cards



Functional Block Diagram

Product Description

The RF6288 is a high-power, high-efficiency dual-path linear amplifier module specifically W-CDMA transmitters used in UMTS mobile systems. This module uses a balanced PA architecture which makes it load insensitive. The device is manufactured on an advanced BiFET HBT process, and was designed for use as the final RF amplifier stage in 3V UMTS handset equipment, spread-spectrum systems, and other transmitter applications. The high band PA frequency coverage is 1710MHz to 1980MHz and the low band PA is 824MHz to 915MHz. The RF6288 has a common analog bias control pin to reduce idle current at lower output power levels. In addition the RF6288 has implemented an integrated power coupler for each PA with good directivity. The RF6288 is assembled in a 28-pin, 4.0mm x 7.0mm, laminate package.

Ordering Information

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|----------------|--|
| RF6288 | 3V Multi-Band UMTS Linear Power Amplifier Module |
| RF6288PCBA-41X | Fully Assembled Evaluation Board |

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|--------------------------------------|--------------------------------------|-------------------------------------|---|
| <input type="checkbox"/> GaAs HBT | <input type="checkbox"/> SiGe BiCMOS | <input type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS | <input type="checkbox"/> Si CMOS | <input checked="" type="checkbox"/> BiFET HBT |
| <input type="checkbox"/> InGaP HBT | <input type="checkbox"/> SiGe HBT | <input type="checkbox"/> Si BJT | <input type="checkbox"/> LD MOS |

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